

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M22-2113		PRIORITY SERIAL NO. 10441334	
LIST OF ART CITED BY APPLICANT <small>(Use several sheets if necessary)</small>				APPLICANT Cem Basceri et al.			
				PRIORITY FILING DATE May 21, 2003		PRIORITY GROUP 319	
U.S. PATENT DOCUMENTS							
*Examiner Initial	Doc Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
MA	AA	5,292,673	03-1994	Shinraki et al.	—	—	—
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MA	AH	6,235,572	05-2001	Kumitono et al.	—	—	—
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FOREIGN PATENT DOCUMENTS							
Doc Number	Date	Country	Class	Subclass	Translation		
					Yes	No	
AK							
AL							
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
MA	AM	Bia Yu, et al., "70nm MOSFET with Ultra-Shallow, Abrupt, and Super-Doped S/D Extension Implemented by Laser Thermal Process (LTP)", IEEE, 03/1999.					
MA	AM	Somit Talwar, et al., "Ultra-Shallow, Abrupt, and Highly-Activated Junctions by Low-Energy Ion Implantation and Laser Annealing", Verdant Technologies, San Jose, CA.					
MA	AD	Ken-ichi Ooto, et al., "Ultra-Low Contact Resistance for Deca-nm MOSFETs by Laser Annealing", IEEE, 09/1999, pps. 20.7.1-20.7.3.					
EXAMINER		Renee K. Day			DATE CONSIDERED 11-1-04		
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

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